

**TITLE OF INVENTION: METHOD AND EQUIPMENT FOR GENERATING
WAFERS BY LASER SLICING OF SiC INGOTS**

ABSTRACT

The present disclosure relates to a wafer generation method, in particular to a method and equipment for generating wafers by laser slicing of SiC ingots. This method improves formation of modified layers and propagation paths of cracks, reduces residual wafer defects, and enhances production yield by adjusting a rotation angle of a SiC ingot and a scanning direction of a laser beam so that the scanning direction of the laser beam deviates from a primary flat within a specific angular range.

FIG. 4